

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SB1079

Silicon PNP Triple Diffused

RENESAS

ADE-208-866 (Z)

1st. Edition

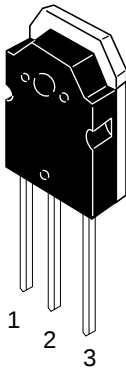
September 2000

Application

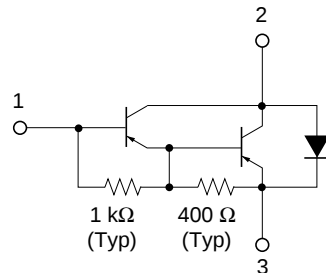
Low frequency power amplifier complementary pair with 2SD1559

Outline

TO-3P



- 1. Base
- 2. Collector (Flange)
- 3. Emitter



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-100	V
Collector to emitter voltage	V_{CEO}	-100	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-20	A
Collector peak current	$I_{C(peak)}$	-30	A
Base current	I_B	-3	A
Collector power dissipation	P_C^{*1}	100	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

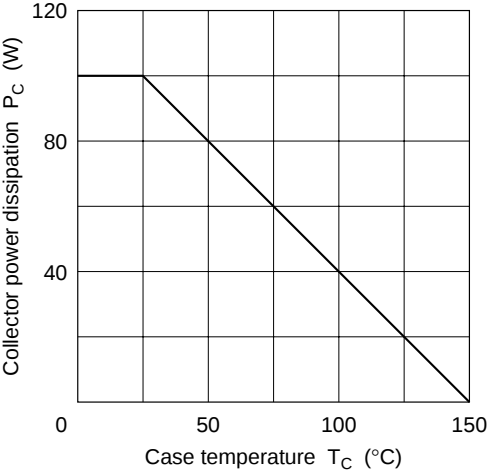
Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

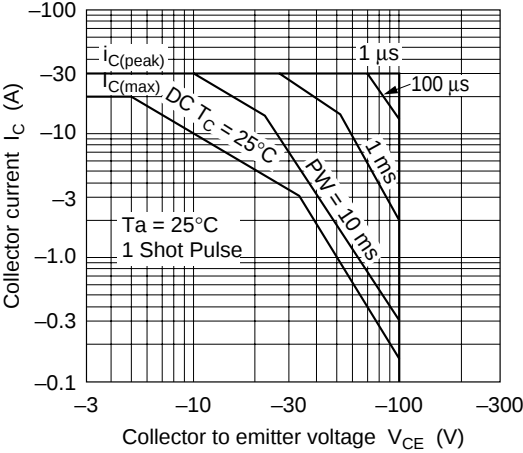
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-100	—	—	V	$I_C = -0.1\text{ mA}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-100	—	—	V	$I_C = -25\text{ mA}$, $R_{BE} = \infty$
Collector to emitter sustain voltage	$V_{CEO(sus)}$	-100	—	—	V	$I_C = -200\text{ mA}$, $R_{BE} = \infty^{*1}$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -50\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-100	μA	$V_{CB} = -100\text{ V}$, $I_E = 0$
	I_{CEO}	—	—	-1.0	mA	$V_{CE} = -80\text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = -3\text{ V}$, $I_C = -10\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	-2.0	V	$I_C = -10\text{ A}$, $I_B = -20\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	-2.5	V	
Collector to emitter saturation voltage	$V_{CE(sat)2}$	—	—	-3.0	V	$I_C = -20\text{ A}$, $I_B = -200\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)2}$	—	—	-3.5	V	
Turn on time	t_{on}	—	0.6	—	μs	$I_C = -10\text{ A}$, $I_{B1} = -I_{B2} = -20\text{ mA}$
Storage time	t_{stg}	—	3.5	—	μs	

Note: 1. Pulse Test.

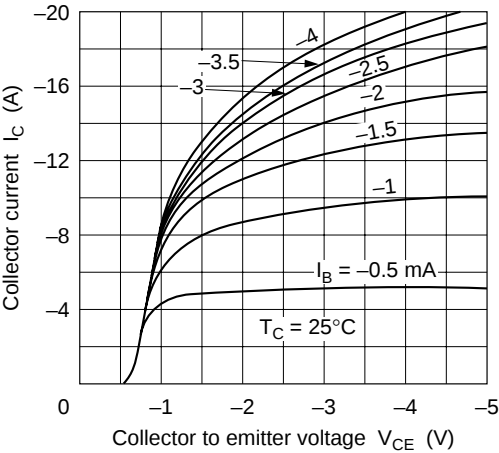
Maximum Collector Dissipation
Curve



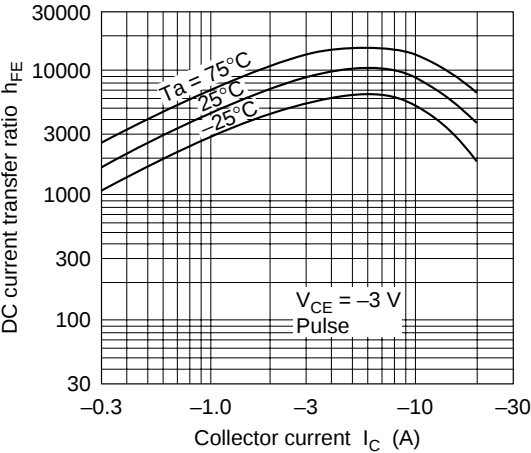
Area of Safe Operation



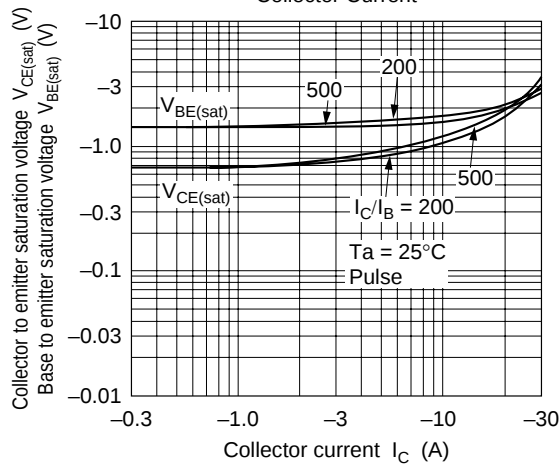
Typical Output Characteristics



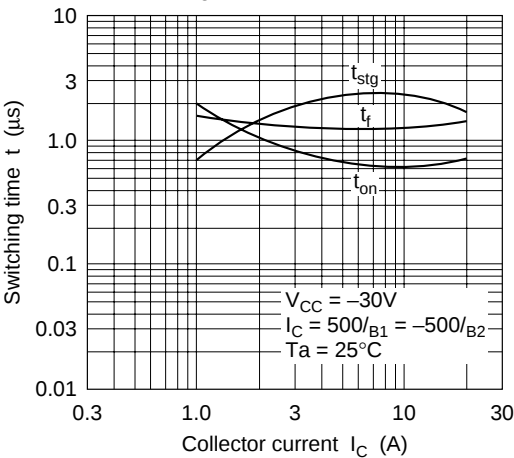
DC Current Transfer Ratio vs.
Collector Current



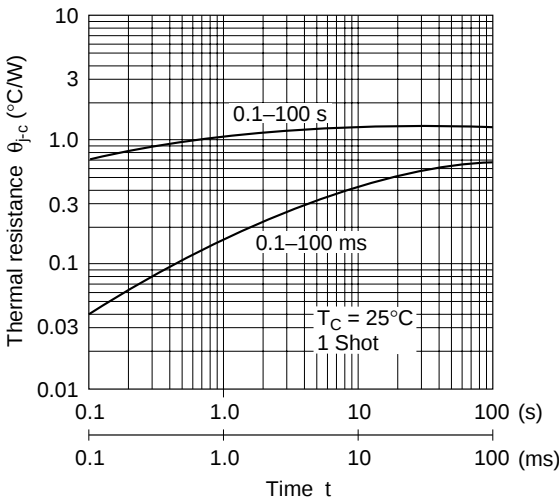
Saturation Voltage vs.
Collector Current



Switching Time vs. Collector Current



Transient Thermal Resistance



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